

isc Silicon NPN Power Transistor

2SC4368

DESCRIPTION

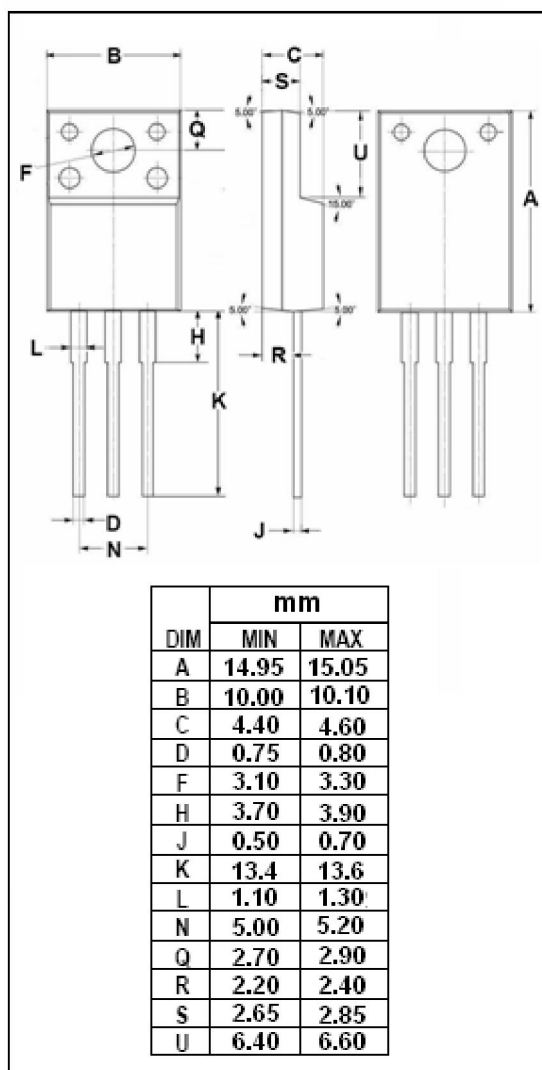
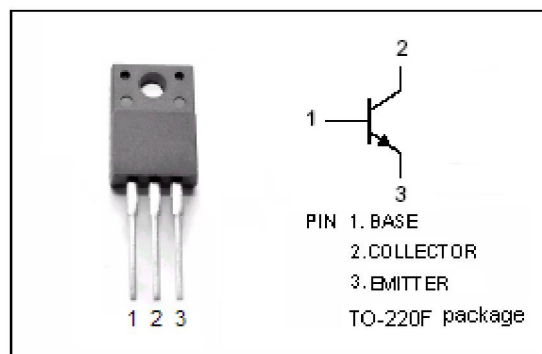
- Collector-Emitter Breakdown Voltage :  $V_{CEO} = 150V(\text{Min})$
- Complement to Type 2SA1657

APPLICATIONS

- Designed for TV, monitor vertical output applications

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	150	V
$V_{CEO}$	Collector-Emitter Voltage	150	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
$I_C$	Collector Current-Continuous	1.5	A
$I_B$	Base Current-Continuous	0.5	A
$P_C$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	20	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistor****2SC4368****ELECTRICAL CHARACTERISTICS**T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	150			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 500mA; I <sub>B</sub> = 50mA			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 120V; I <sub>E</sub> = 0			10	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			10	μ A
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 500mA; V <sub>CE</sub> = 10V	40		140	
C <sub>OB</sub>	Collector Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1.0MHz		35		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 500m A; V <sub>CE</sub> = 10V		4		MHz